








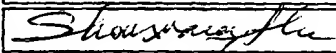
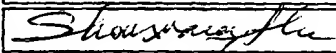
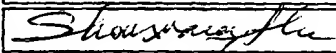


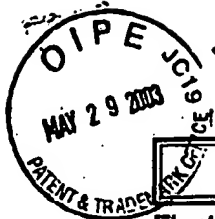
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ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

Stylesheet Version v18.0

Title of Invention	High-Voltage Transistor With A Multi-Layer Conduction Region																								
<div>Application Number: 09/961229</div> <div>Confirmation Number: 4375</div> <div>First Named Applicant: Vladimir Rumennik</div> <div>Attorney Docket Number: 03692.P007XD4</div> <div>Art Unit: 2811</div> <div>Examiner: Shouxiang Hu</div> <div>Search string: (6633065 or 6639277).pn.</div> <div></div> <div>RECEIVED NOV 28 2003 TECHNOLOGY CENTER 2806</div>																									
US Patent Documents																									
Note: Applicant is not required to submit a paper copy of cited US Patent Documents																									
<table border="1"><thead><tr><th>init</th><th>Cite.No.</th><th>Patent No.</th><th>Date</th><th>Patentee</th><th>Kind</th><th>Class</th><th>Subclass</th></tr></thead><tbody><tr><td></td><td>1</td><td>6633065</td><td>2003-10-14</td><td>Rumennik et al.</td><td>B2</td><td></td><td></td></tr><tr><td></td><td>2</td><td>6639277</td><td>2003-10-28</td><td>Rumennik et al.</td><td>B2</td><td></td><td></td></tr></tbody></table>		init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass		1	6633065	2003-10-14	Rumennik et al.	B2				2	6639277	2003-10-28	Rumennik et al.	B2		
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Note: Remarks are not for responding to an office action.																									
This information disclosure statement is being submitted concurrent with the filing of a Request for Continued Examination in the above-referenced application.																									
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